NEW PRODUCT

DMN2026UVT

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D T_A = +25°C
20V	24mΩ @ V_{GS} = 4.5V	6.2A
	32mΩ @ V_{GS} = 2.5V	

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

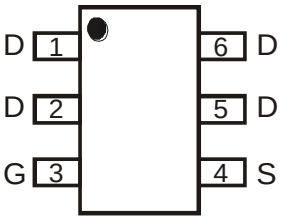
- DC-DC Converters
- Power Management Functions
- Backlighting

Mechanical Data

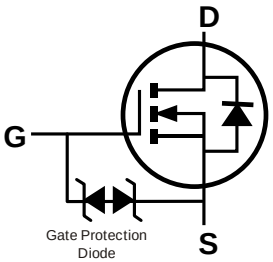
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.013 grams (Approximate)

TSOT26

Top View



Top View
Pin Configuration



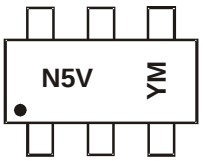
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2026UVT-7	TSOT26	3,000/Tape & Reel
DMN2026UVT-13	TSOT26	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N5V = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: B = 2014)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C	I_D	6.2	A
Maximum Body Diode Forward Current (Note 6)			I_S	2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	20	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.15	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	107	°C/W
	t<10s		76	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.75	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	75	°C/W
	t<10s		50	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	16	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	—	1.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	18	24	mΩ	V_{GS} = 4.5V, I_D = 6.2A
		—	21	32		V_{GS} = 2.5V, I_D = 5.2A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1.3A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	887	—	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	91	—		
Reverse Transfer Capacitance	C_{rss}	—	37	—		
Gate Resistance	R_g	—	191	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	10	—	nC	V_{DS} = 10V, I_D = 6.5A
Total Gate Charge (V_{GS} = 8V)	Q_g	—	18.4	—		
Gate-Source Charge	Q_{gs}	—	1.3	—		
Gate-Drain Charge	Q_{gd}	—	1.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	53	—	ns	V_{DS} = 10V, V_{GS} = 4.5V, R_G = 6Ω, R_L = 10Ω, I_D = 1A
Turn-On Rise Time	t_R	—	66	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	619	—		
Turn-Off Fall Time	t_F	—	197	—		
Reverse Recovery Time	t_{RR}	—	119	—	ns	I_F = 4A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—-	96	—	nC	I_F = 4A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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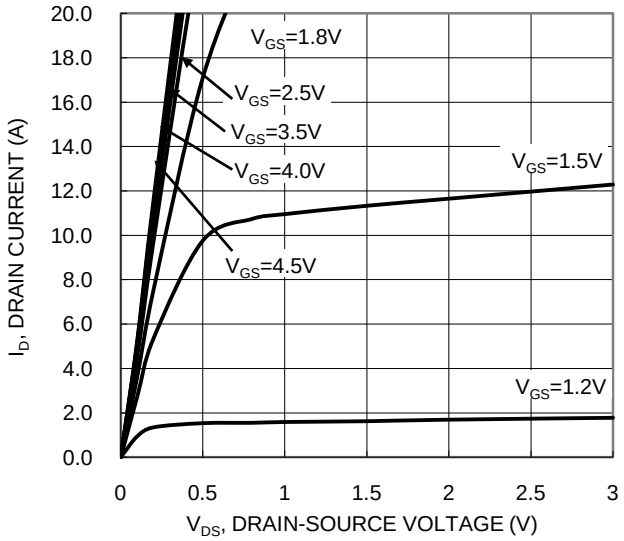

Figure 1. Typical Output Characteristic

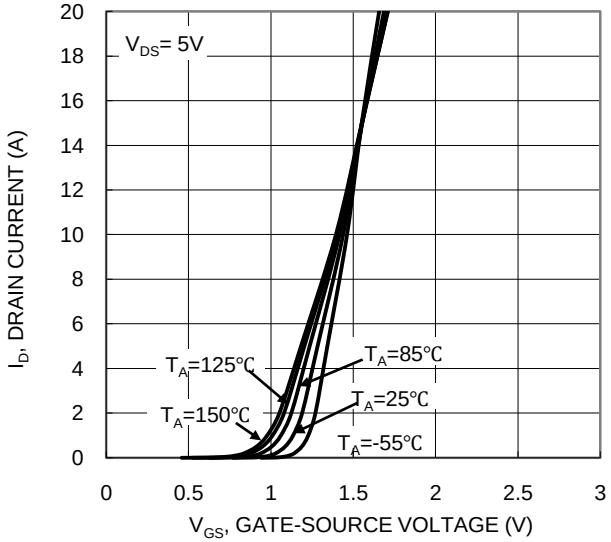

Figure 2. Typical Transfer Characteristic

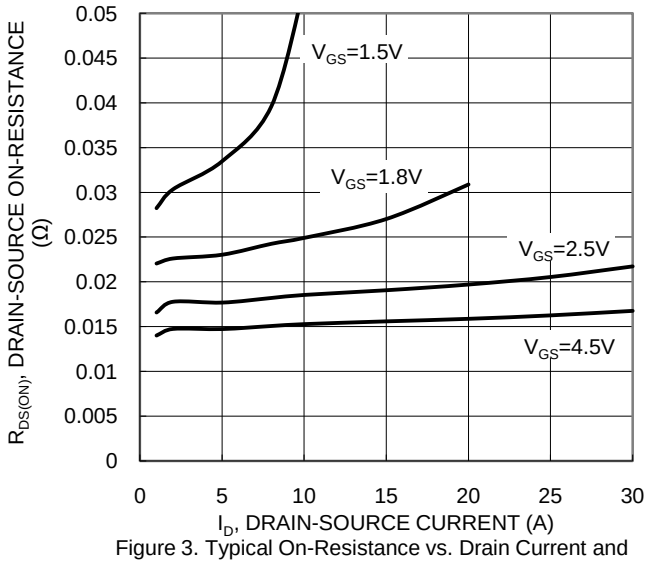

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

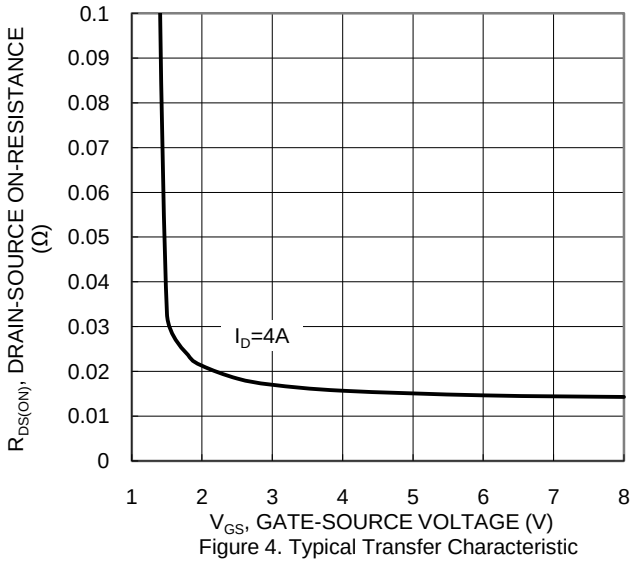

Figure 4. Typical Transfer Characteristic

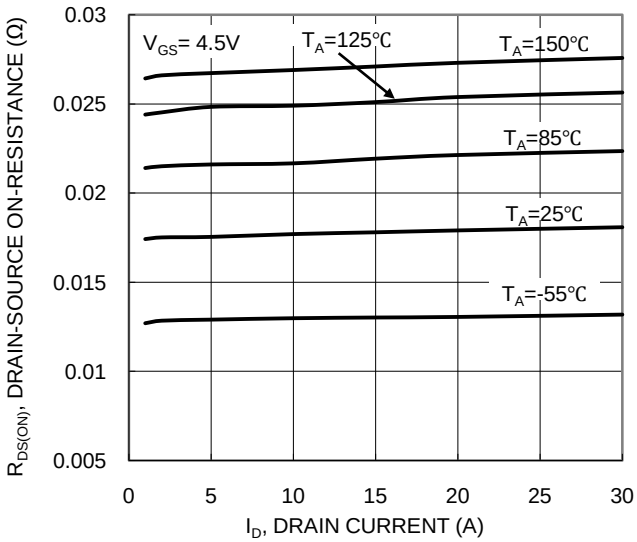

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

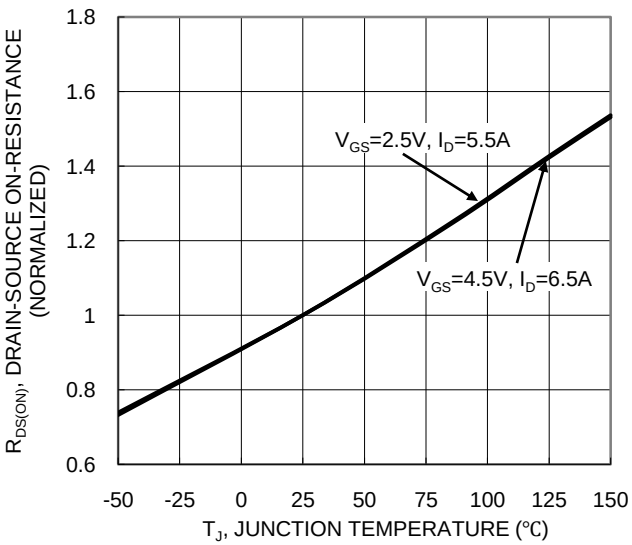

Figure 6. On-Resistance Variation with Temperature

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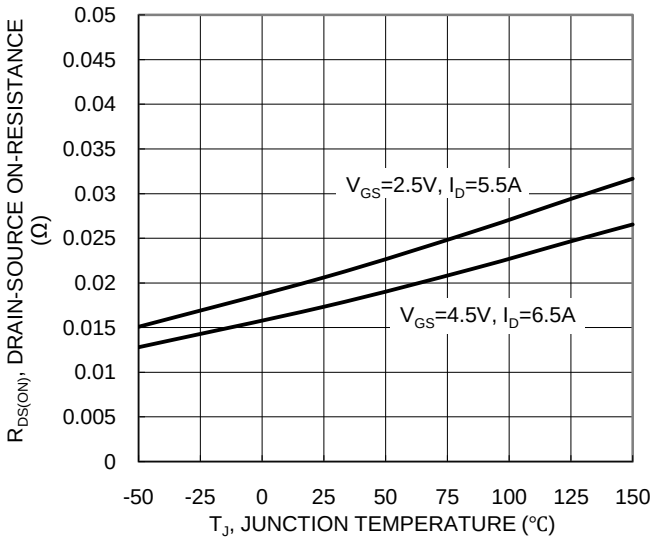

Figure 7. On-Resistance Variation with Temperature

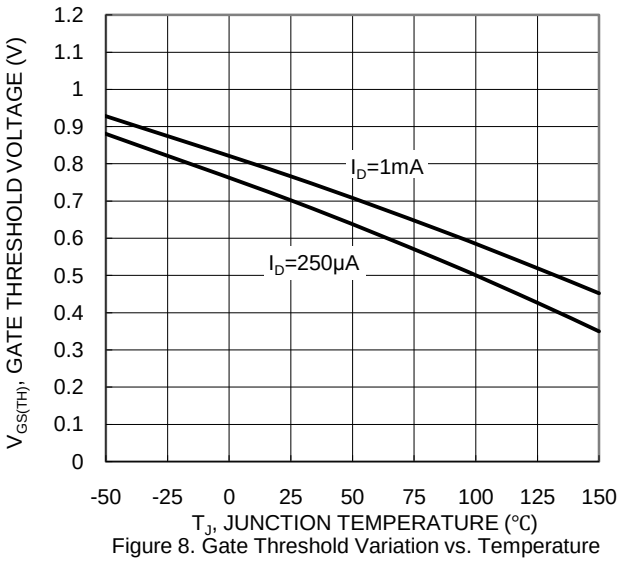

Figure 8. Gate Threshold Variation vs. Temperature

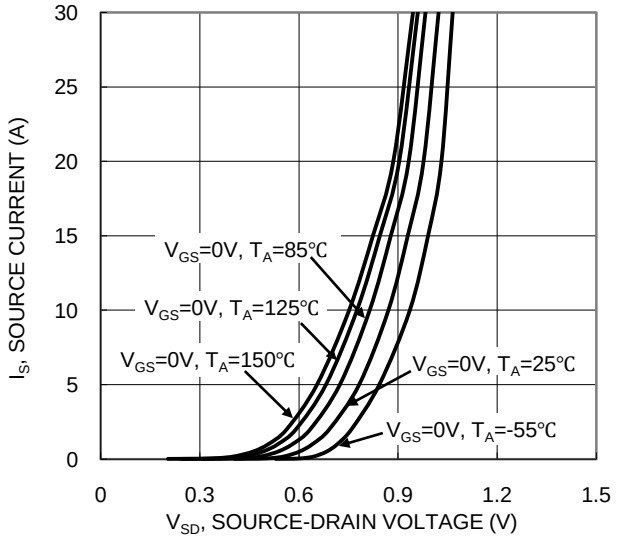

Figure 9. Diode Forward Voltage vs. Current

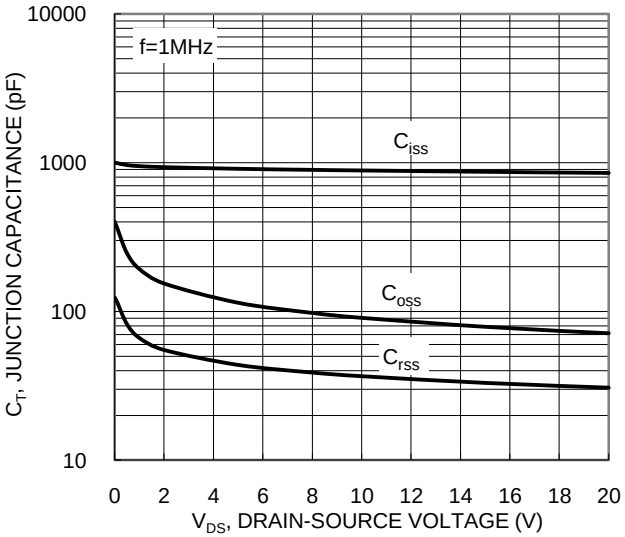

Figure 10. Typical Junction Capacitance

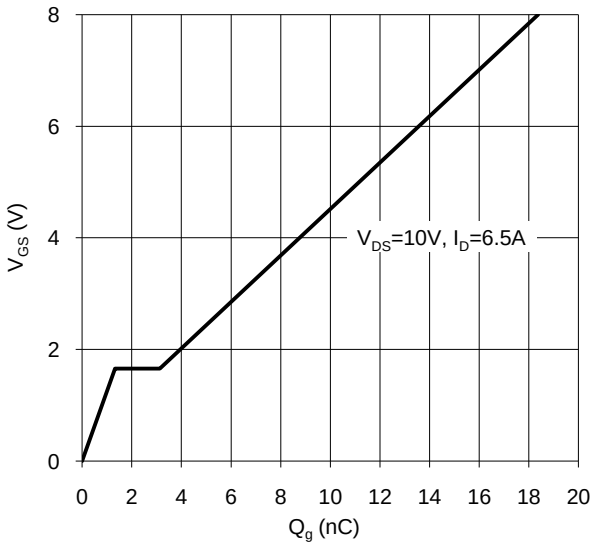

Figure 11. Gate Charge

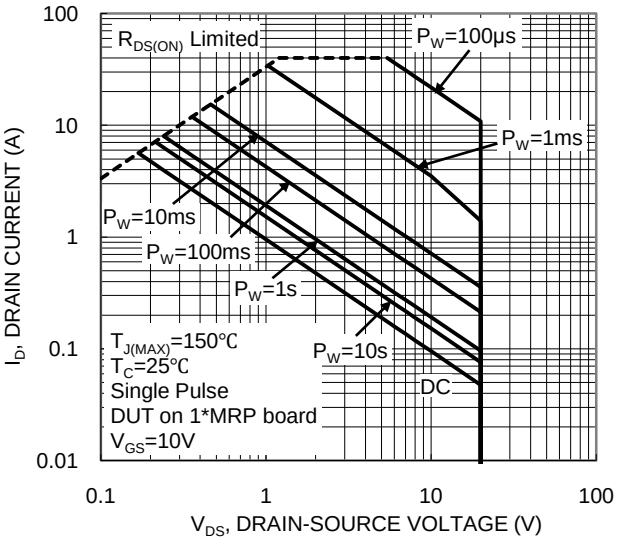

Figure 12. SOA, Safe Operation Area

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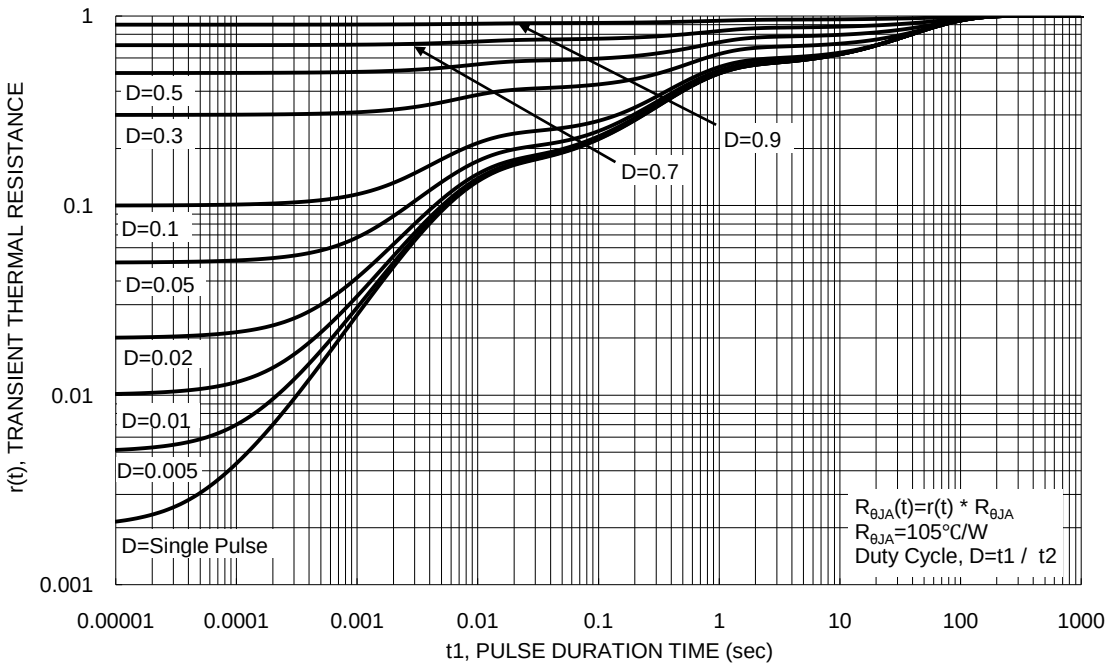
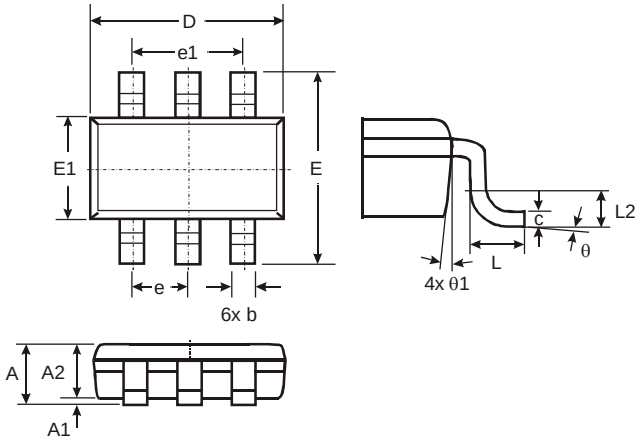


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TSOT26			
Dim	**Min**	**Max**	**Typ**
A	—	1.00	—
A1	0.01	0.10	—
A2	0.84	0.90	—
D	—	—	2.90
E	—	—	2.80
E1	—	—	1.60
b	0.30	0.45	—
c	0.12	0.20	—
e	—	—	0.95
e1	—	—	1.90
L	0.30	0.50	—
L2	—	—	0.25
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

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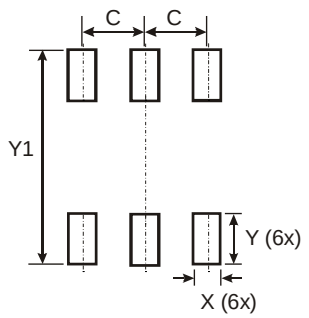
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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